

ABSTRACT OF THE DISCLOSURE

A method and an apparatus utilized for thermal processing of substrates during semiconductor manufacturing. The method includes heating the substrate to a predetermined temperature using a heating assembly, cooling the substrate to the predetermined temperature using a cooling assembly located such that a thermal conductance region is provided between the heating and cooling assemblies, and adjusting a thermal conductance of the thermal conductance region to aid in heating and cooling of the substrate. The apparatus includes a heating assembly, a cooling assembly located such that a thermal conductance region is provided between the heating and cooling assemblies, and a structure or configuration for adjusting a thermal conductance of the thermal conductance region.

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